

SELECTIVE SALICIDATION METHODS

Abstract

Methods for selective salicidation of a semiconductor device. The invention implements a chemical surface pretreatment by immersion in ozonated water H_2O prior to metal deposition. The pretreatment forms an interfacial layer that prevents salicidation over an n-type structure. As a result, the invention does not add any additional process steps to the conventional salicidation processing.